



General Description

The HSSX2303 is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The HSSX2303 meet the RoHS and Green Product requirement with full function reliability approved.

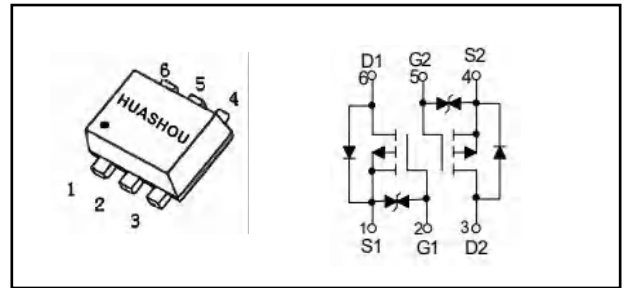
Features

- Super Low Gate Charge
- Low Threshold
- High-Side Switching
- Advanced high cell density Trench Technology
- ESD Protected up to 2KV

Product Summary

V_{DS}	-20	V
$R_{DS(ON),Max}$	800	mΩ
I_D	-0.8	A

SOT-563 Pin Configurations



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 8	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-0.8	A
I_{DM}	Pulsed Drain Current ²	-3	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	0.15	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	800	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.014	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-0.8A	---	600	800	mΩ
		V _{GS} =-2.5V, I _D =-0.6A	---	800	1000	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.67	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3.95	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±10	uA
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-0.8A	---	18	---	nC
Q _{gs}	Gate-Source Charge		---	4.2	---	
Q _{gd}	Gate-Drain Charge		---	2.6	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-6V, V _{GS} =-4.5V, R _G =6Ω, I _D =-0.8A	---	6	---	ns
T _r	Rise Time		---	12	---	
T _{d(off)}	Turn-Off Delay Time		---	25	---	
T _f	Fall Time		---	6.8	---	
C _{iss}	Input Capacitance	V _{DS} =-6V, V _{GS} =0V, f=1MHz	---	145	---	pF
C _{oss}	Output Capacitance		---	115	---	
C _{rss}	Reverse Transfer Capacitance		---	10	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

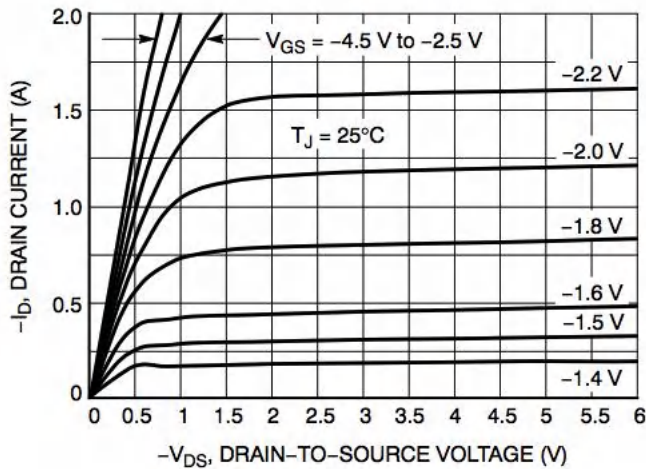


Figure 1. On-Region Characteristics

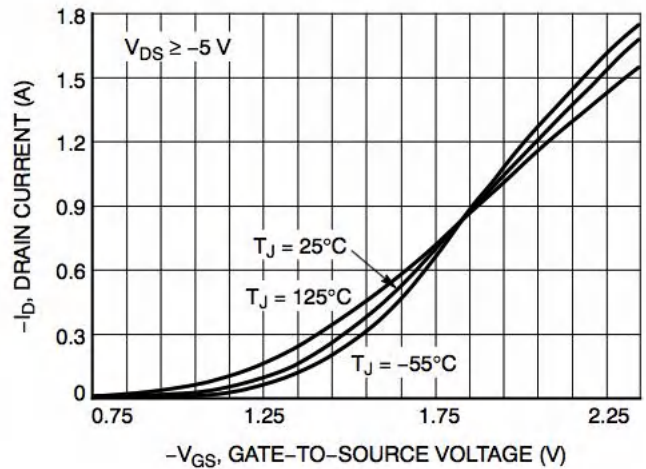


Figure 2. Transfer Characteristics

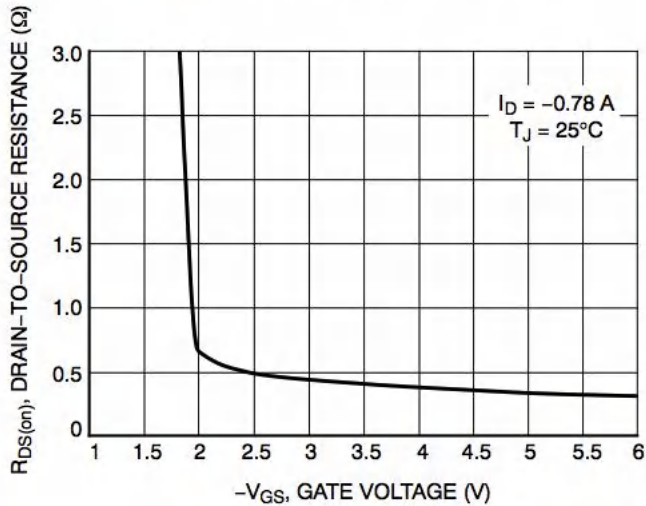


Figure 3. On-Resistance vs. Gate-to-Source Voltage

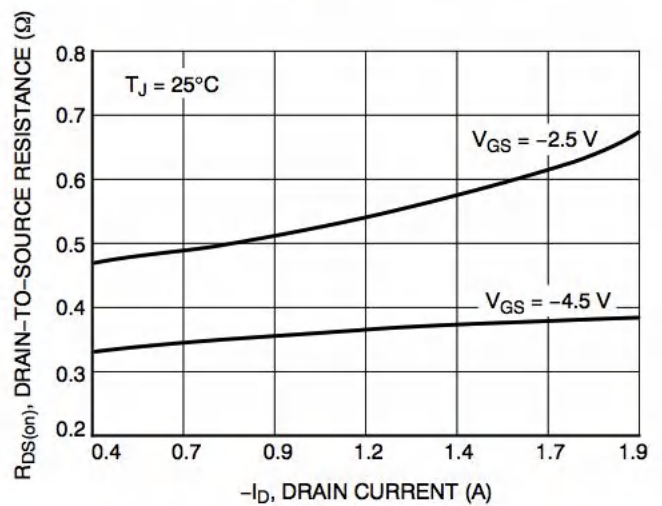


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

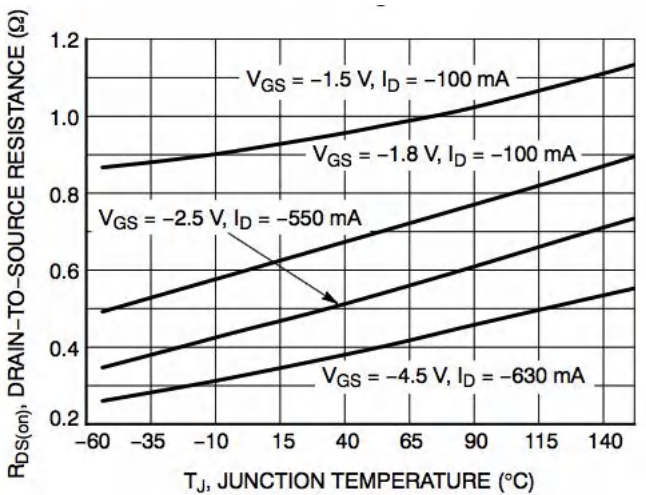


Figure 5. On-Resistance Variation with Temperature

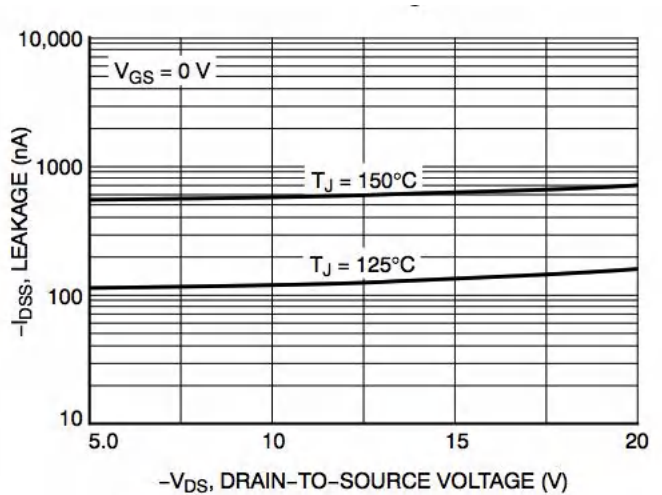


Figure 6. Drain-to-Source Leakage Current vs. Voltage

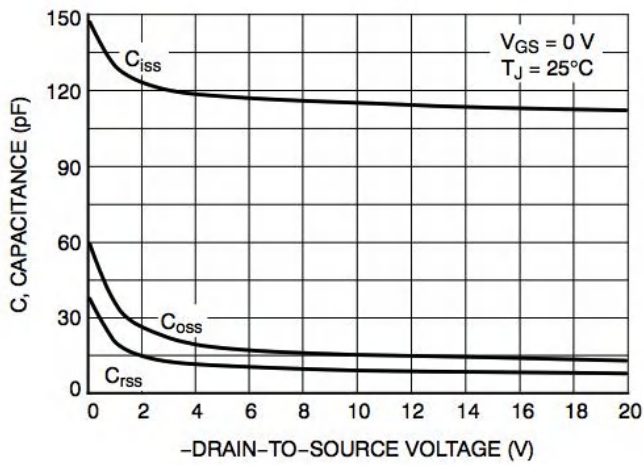


Figure 7. Capacitance Variation

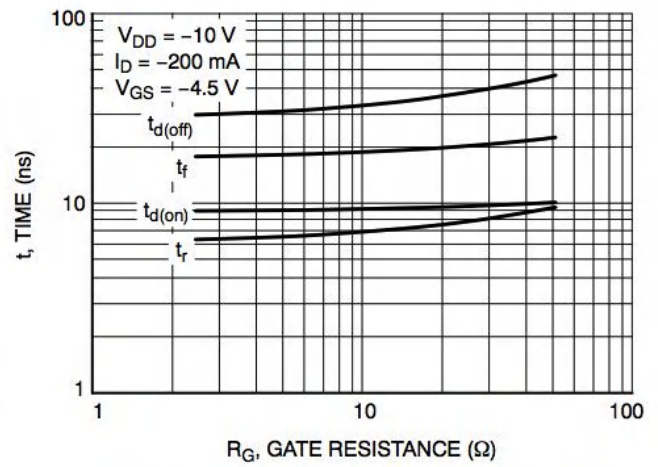


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

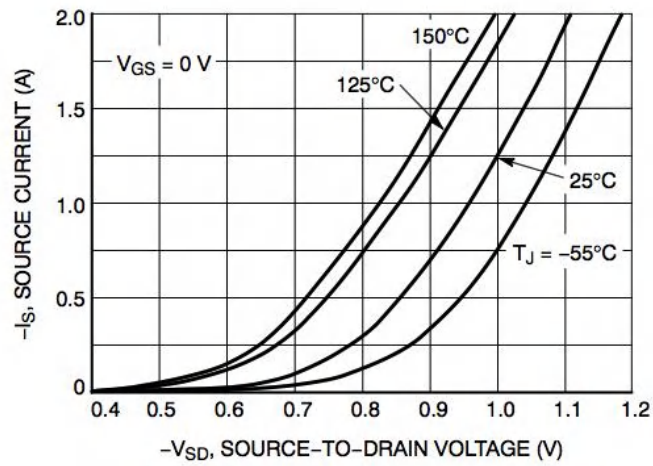


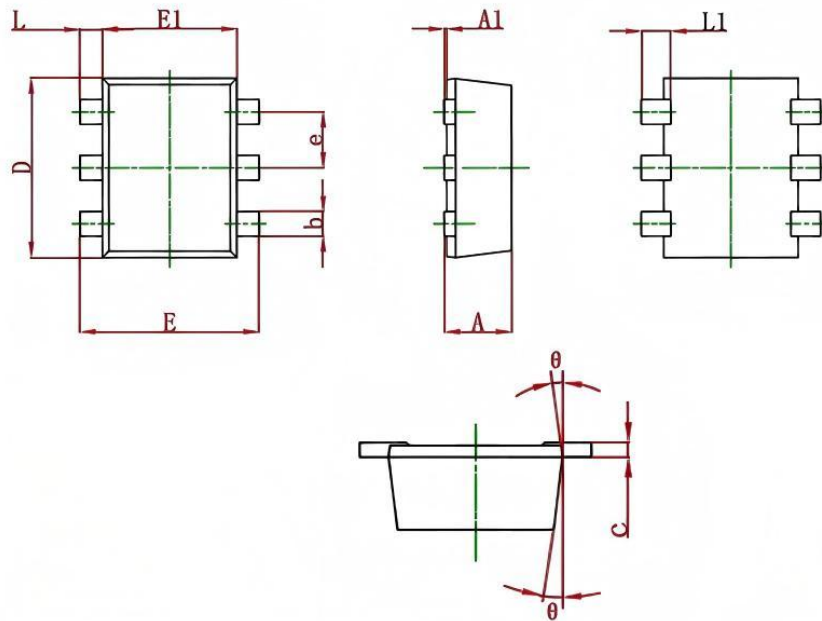
Figure 9. Diode Forward Voltage vs. Current



Ordering Information

Part Number	Package code	Packaging
HSSX2303	SOT-563	3000/Tape&Reel

SOT-563 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
AI	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
C	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
EI	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7 °REF.		7 °REF.	



HSSX2303 TOP Marking

7807



Part Number